L Number	Hits	Search Text	DB	Time stamp
2	13	20030107465.pn. 20030022102.pn. 20020197834.pn.	USPAT;	2004/06/24 09:08
_		6465742.pn. 20020004180.pn. 6565764.pn. 6709806.pn.	US-PGPUB; DERWENT	
3	6	jp-07207450-\$.did. jp-11025755-\$.did. jp-10149722-\$.did.	USPAT; US-PGPUB;	2004/06/24 09:14
			EPO; JPO; DERWENT	
4	1	2001jp-0170018.ap,prai. 2001jp-0295461.ap,prai.	USPAT; US-PGPUB;	2004/06/24 09:35
			EPO; JPO; DERWENT	
5	4	4895756.pn. 5819858.pn. 6504685.pn. 20020157862.pn.	USPAT; US-PGPUB	2004/06/24 10:30
13	7	ASAKAWA-KOJI and HOTTA-YASUYUKI and	USPAT;	2004/06/24 11:34
		MATAKE-SHIGERU and HIRAOKA-TOSHIRO	US-PGPUB; EPO; JPO;	
14	16	5731073.uref. 5910354.uref.	DERWENT USPAT;	2004/06/24 11:35
- '		·	US-PGPUB	
15	16	(((porous pore void) near2 (insulator material substrate dielectric semiconductor)) same ((conduct\$4 metal) near2	USPAT; US-PGPUB	2004/06/24 11:39
		(infiltrat\$4 impregnat\$4))) and (expos\$4 with beam)	O3-FGFOD	
16	0	6649516.URPN.	USPAT	2004/06/24 11:42
17	363	(((porous pore void) near2 (insulator material substrate	USPAT;	2004/06/24 11:43
		dielectric semiconductor)) same ((conduct\$4 metal) near2	US-PGPUB	
		(infiltrat\$4 impregnat\$4))) and (via feedthrough throughhole wiring interconnect trace)		
18	14	(((porous pore void) near2 (insulator material substrate	EPO; JPO;	2004/06/24 12:09
		dielectric semiconductor)) and ((conduct\$4 metal) near2	DERWENT;	
		(infiltrat\$4 impregnat\$4))) and (via feedthrough	IBM_TDB	
19	22	throughhole wiring interconnect trace) (((porous pore void) near2 (insulator material substrate	USPAT;	2004/06/24 12:12
19		dielectric semiconductor)) and ((conduct\$4 metal) near2	US-PGPUB	2001/00/2112:12
		(infiltrat\$4 impregnat\$4))) and (438/638.ccls. 29/829.ccls.		
		29/846.ccls. 29/880.ccls. 174/262.ccls. 200/264.ccls.		
20	264	361/748.ccls.)	USPAT;	2004/06/24 12:24
20	261	(((porous pore void) near2 (insulator material substrate dielectric semiconductor)) and ((conduct\$4 metal) near2	US-PGPUB	2004/00/24 12.24
		(infiltrat\$4 impregnat\$4))) and (via feedthrough	00 : 0; 02	
		throughhole) and (wiring interconnect trace)		
21	280	(438/638.ccls. 29/829.ccls. 29/846.ccls. 29/880.ccls.	USPAT;	2004/06/24 13:21
		174/262.ccls. 200/264.ccls. 361/748.ccls.) and (((porous pore void) near2 (insulator material substrate dielectric	US-PGPUB	
		semiconductor)) ((conduct\$4 metal) near2 (infiltrat\$4		
		impregnat\$4)))		
22	0	6608757.URPN.	USPAT	2004/06/24 13:11
23	6754	257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls.	USPAT;	2004/06/24 13:20
		200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls. 430/5.ccls. 430/269.ccls.	US-PGPUB	
24	292	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls.	USPAT;	2004/06/24 16:32
		200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls.	US-PGPUB	, ,=:====
		430/5.ccls. 430/269.ccls.) and (((porous pore void) near2		
		(insulator material substrate dielectric semiconductor))		
25	40	((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) (257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls.	USPAT;	2004/06/24 13:22
23	70	200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls.	US-PGPUB	200 1/00/27 13.22
		430/5.ccls. 430/269.ccls.) and ((porous pore void) near2		
		(insulator material substrate dielectric semiconductor)) and		
		((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))	<u> </u>	<u>L.,,,,</u>

26	90	(257/775.ccls. 257/e23.169.ccls. 257/e23.174.ccls.	USPAT;	2004/06/24 13:28
		200/264.ccls. 428/550.ccls. 428/566.ccls. 174/262.ccls.	US-PGPUB	
		430/5.ccls. 430/269.ccls.) and (((porous pore void) near2		
		(insulator material substrate dielectric semiconductor))		
		((conduct\$4 metal) near2 (infiltrat\$4 impregnat\$4))) and		
		(mask photomask)		
27	14	((F - · · · · F - · · · · · · · · · · · ·	USPAT;	2004/06/24 14:42
		dielectric semiconductor)) same ((conduct\$4 metal) near2	US-PGPUB	
		(infiltrat\$4 impregnat\$4)) same (mask photomask)		
28	174	((porous pore void) near2 (insulator material substrate	USPAT;	2004/06/24 15:57
		dielectric semiconductor)) and ((conduct\$4 metal) near2	US-PGPUB	
		(infiltrat\$4 impregnat\$4)) and (mask photomask)		
29	446	(((porous pore void) near2 (insulator material substrate	EPO; JPO;	2004/06/24 15:56
		dielectric semiconductor)) ((conduct\$4 metal) near2	DERWENT;	
		(infiltrat\$4 impregnat\$4))) and (mask photomask)	IBM_TDB	
30	10	((porous pore void) with (insulator material substrate	EPO; JPO;	2004/06/24 15:59
		dielectric semiconductor)) and ((conduct\$4 metal) with	DERWENT;	
		(infiltrat\$4 impregnat\$4)) and (mask photomask)	IBM_TDB	
31	292	(((porous pore void) with (insulator material substrate	EPO; JPO;	2004/06/24 16:00
		dielectric semiconductor)) same (conduct\$4 metal infiltrat\$4	DERWENT;	
		impregnat\$4)) and (mask photomask)	IBM_TDB	2004/05/2445 00
32	234	((porous pore void) with (insulator material substrate	EPO; JPO;	2004/06/24 16:00
		dielectric semiconductor) with (conduct\$4 metal infiltrat\$4	DERWENT;	
		impregnat\$4)) and (mask photomask)	IBM_TDB	2004/06/24 16:01
33	92	(((porous pore void) near2 (insulator material substrate	EPO; JPO;	2004/06/24 16:01
		dielectric semiconductor)) same (conduct\$4 metal infiltrat\$4	DERWENT;	
	20	impregnat\$4)) and (mask photomask)	IBM_TDB	2004/06/24 16:22
34	39	430/5.ccls. and (((porous pore void) near2 (insulator	USPAT;	2004/06/24 16:32
		material substrate dielectric semiconductor)) ((conduct\$4	US-PGPUB	
i		metal) near2 (infiltrat\$4 impregnat\$4)))	<u> </u>	l